SANGDEST MICROELECTRONICS

Technical Data Data Sheet N0131, Rev. C

MBRF20200CT(CTR) SCHOTTKY RECTIFIER

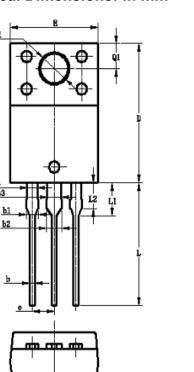
Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Features:

- 175°C TJ operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions: In mm



	OPTION 1(CJ)		OPTION 2(HD	
Dim	Min	Мах	Min	Max
Α	4.35	4.65	4.30	4.70
b	0.50	0.75	0.50	0.75
b1	1.15	1.402	1.20	1.45
b2	1.55	1.802	1.60	1.85
b3	1.55	1.65	1.50	1.75
b4	1.10	1.35	1.10	1.35
С	0.50	0.75	0.55	0.75
D	14.8	15.2	14.80	15.20
Е	10.06	10.26	9.96	10.36
е	2.46	2.62	2.55	ТҮР
F	2.85	3.15	2.80	3.20
G	6.50	6.90	6.50	6.90
L	12.70	13.70	12.70	13.70
L1	3.40	3.80	3.40	4.00
L2	2.60	3.00	-	-
Q	2.60	2.80	2.50	2.90
Q1	2.50	2.90	2.50	2.90
ØR	3.40	3.60	3.30	3.70

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MBRF20200CT

MBRF20200CTR

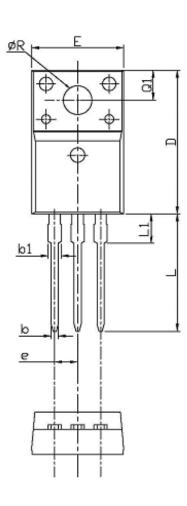
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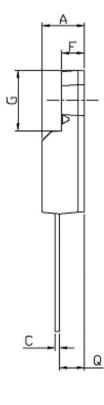
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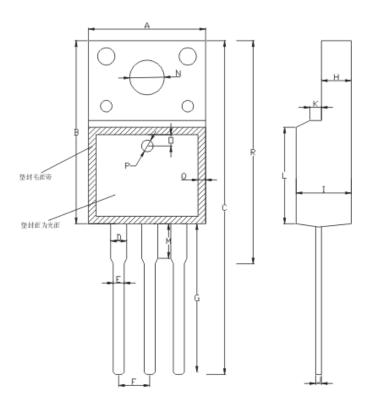


	OPTION 3		OPTION 4	
Dim	Min	Max	Min	Max
Α	4.53	4.93	4.50	4.90
b	0.71	0.91	0.70	0.90
b1	1.15	1.39	1.33	1.47
С	0.36	0.53	0.45	0.60
D	15.67	16.07	15.67	16.07
E	9.96	10.36	9.96	10.36
е	2.54TYP		2.54 BSC	
F	2.34	2.76	2.34	2.74
G	6.50	6.90	6.48	6.88
L	12.37	12.77	12.78	13.18
L1	2.23	2.63	3.03	3.43
Q	2.56	2.96	2.56	2.96
Q1	3.10	3.50	3.10	3.50
ØR	2.98	3.38	3.08	3.28

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A:10.20	± 0.50	B:15.90	± 0.50	C:29.00	± 1.00	D:1.24	± 0.10
E:0.80	± 0.10	F:2.54	± 0.10	G:13.10	$\pm 1,0$	H:2.55	± 0.05
I:4.70	± 0.05	J:0.50	± 0.05	K:1.20	± 0.20	L:8.00	± 0.50
M:3.00	± 0.50	N:3.20	± 0.20	O:1,25	± 0.05	P:1.5	± 0.05
Q:1.0	±0.20	R:19.2	±1.0				

OPTION 5 (SR)

ITO-220AB



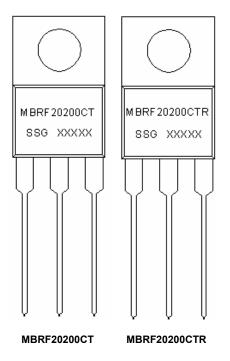
Technical Data

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Marking Diagram:



Where XXXXX is YYWWL

MBR	= Device Type
F	= Package Type
20	= Forward Current (20A)
200	= Reverse Voltage (200V)
CT/CTR	= Configuration
SSG	= SSG
YY	= Year
WW	= Week
L	= Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
MBRF20200CT	ITO-220AB (Pb-Free)	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V _{RWM}	-	200	V
Average Forward Current	I _{F(AV)}	50% duty cycle @T _c =105°C,	10(Per leg)	A
		rectangular wave form	20(Per device)	
Peak Repetitive Forward Current(per leg)	I _{FRM}	Rated V _R , Square wave,20KHz, @T _c =90°C	20	А
Peak One Cycle Non- Repetitive Surge Current (per leg)	I _{FSM}	8.3 ms, half Sine pulse	150	A

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Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop	V_{F1}	@ 10A, Pulse, T _J = 25 °C	0.95	V
(per leg) *	V_{F2}	@ 10A, Pulse, T _J = 125 °C	0.85	V
Reverse Current at DC condition (per leg)	I _{R1}	@V _R = rated V _R T _J = 25 °C	1.0	mA
Reverse Current (per leg) *	I _{R2}	@V _R = rated V _R T _J = 125 °C	50	mA
Junction Capacitance (per leg)	CT	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	300	pF
Series Inductance(per leg)	Ls	Measured lead to lead 5 mm from package body	8.0	nH
Voltage Rate of Change	dv/dt	-	10,000	V/µs

* Pulse Width < 300µs, Duty Cycle <2%

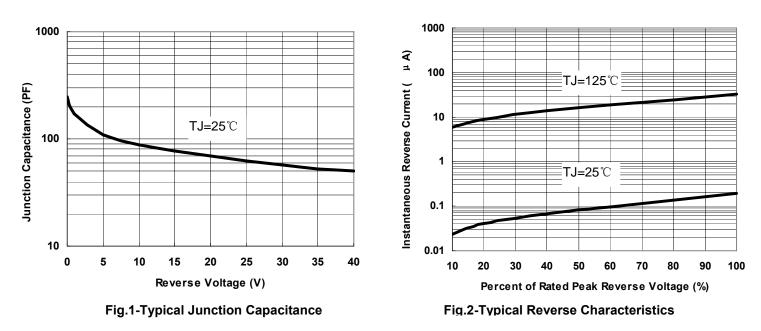
Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature Range	TJ	-	-55 to +175	°C
Storage Temperature Range	T _{stg}	-	-55 to +175	°C
Maximum Thermal Resistance Junction to Case (per leg)	$R_{ ext{ heta}JC}$	DC operation	4.5	°C/W
Approximate Weight	wt	-	2	g
Case Style		ITO-220AB		

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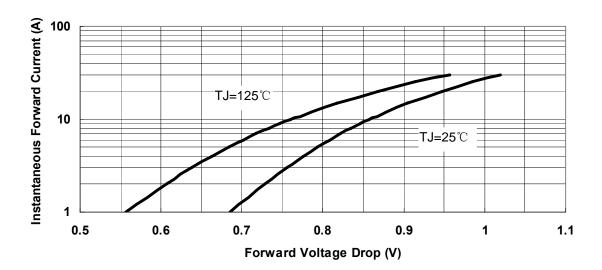
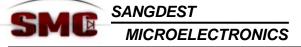


Fig.3-Typical Instantaneous Forward Voltage Characteristics



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